

<b>SANYO</b>	No.2434	<b>2SD1887</b>
NPN Triple Diffused Planar Silicon Transistor <b>Color TV Horizontal Deflection</b> <b>Output Applications</b>		

**Applications**

- . Color TV horizontal deflection output
- . Color display horizontal deflection output

**Features**

- . High speed ( $t_f=100ns$  )
- . high breakdown voltage ( $V_{CBO}=1500V$ )
- . High reliability (adoption of HVP process)

**Absolute Maximum Ratings at Ta=25°C**

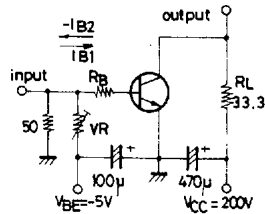
			unit
Collector-to-Base Voltage	$V_{CBO}$	1500	V
Collector-to-Emitter Voltage	$V_{CEO}$	800	V
Emitter-to-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	10	A
Collector Current (Pulse)	$I_{CP}$	30	A
Collector Dissipation	$I_C$	70	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	$I_{CES}$	$V_{CE}=1500V$			1.0	mA
	$I_{CBO}$	$V_{CB}=800V$			10	µA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C=100mA, I_B=0$	800			V
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4V$			1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=8A, I_B=1.6A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=8A, I_B=1.6A$			1.5	V
DC Current Gain	$h_{FE1}$	$V_{CE}=5V, I_C=1A$		8		
	$h_{FE2}$	$V_{CE}=5V, I_C=8A$		5	10	
Fall Time	$t_f$	$I_C=6A, I_{B1}=1.2A, I_{B2}=-2.4A$		0.1	0.3	µs

**Switching Time Test Circuit**

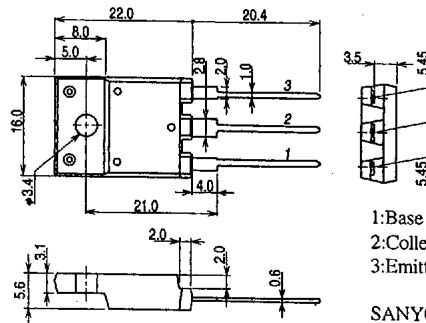
PW=20µs, duty ≤ 1%



Unit (resistance:Ω, capacitance:F)

**Package Dimensions 2039D**

(unit:mm)



1:Base  
2:Collector  
3:Emitter

SANYO:TO3PML

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